Form PTO 1	449	U.S. DEPARTMENT	OF COMMERCE	ATTY DOCKET NO.		SERIAL NO.			
(Modified)		PATENT AND TRADEMARK OFFICE		251475US3DIV		New Application			
				APPLICANT					
LIST	OF REFE	RENCES CITED BY AF	PLICANT	Kousaku MATSUNO, et al.					
				FILING DATE		GROUP			
				Herewith					
U.S. PATENT DOCUMENTS									
EXAMINE INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
MK	AA	6,080,531	06/27/00	Carter et al.					
1	AB	5,971,368	10/26/99	Nelson et al.					
	AC	5,983,909	11-1999	Yeol et al.					
	AD	6,920,777	09-2001	lmaoka et al.					
	AE	6,325,359	12-2001	Haga et al.					
	AF	5,503,708	04-1996	Koizumi et al.					
	AG	6,086,057	07-2000	Mitsumori et al.					
	AH	6,039,815	03-2000	Yeol et al.	1				
10	Al	6,035,871	03-2000	Eui-Yeol, Oh	-				
	AJ	4,812,201	03-1989	Sakai et al.		_			
	AK	5,783,790	07-1998	Mitsumori et al.					
	AL	6,217,665	04-2001	Suzuki					
MK	АМ	5.739,575	04-1998	Numano et al.		-			
	AN								
			FOI	REIGN PATENT DOCUMENTS	<u> </u>	L			
	DOCUMENT TRANSLATION								
		NUMBER DATE COUNTRY			TRANSLATION YES NO				
MIC		8-78372	03-1996	Japan (w/ abstract)	-		xx		
MIK	AP	63-271938	11-1988	Japan (w/ abstract)			xx		
	AQ	, 0.0 s.	The same of the same of the same of						
	AR								
	AS								
	AT				~				
	AU								
	AV		_ <						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)									
MK	AW	S. Nelson: Using an ozone water last cleaning process to research the effects of process parameters on water contamination; SPWCC, pp. 230-242, March 4-7, 1996							
i	AX	M. Hiroshi et al.: Dissolved-Gas Controlled Ultrapure Water Production System for Wet Cleaning Processes; The seventh International symposium on semiconductor manufacturing, proceedings of ISSM '98, Tokyo, pp. 428-431 (1998)							
	AY	M. Hiroshi et al.: Advanced UCT Cleaning Process Based on Specific Gases Dissolved Ultrapure Water; The eighth International symposium on semiconductor manufacturing, proceedings of ISSM '99 Tokyo, pp. 453-456 (1999)							
MC	AZ	M. Hiroshi et al.: Development of ozonated ultra-pure water supplying system using direct-dissolving method, SPWCC, pp. 51-60, March 13-16,							
Examiner 2000					Date Considered (2) / (2.7./(2.1.)				
Examiner. Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in onformance and not considered. Include copy of this form with next communication to applicant.									
ISEDIEMMINISES (1251475) 14440 000									

Form PTO 1449		U.S. DEPARTMENT OF COMMERCE	ATTY DOCKET NO.	SERIAL NO.					
(Modified)		PATENT AND TRADEMARK OFFICE	251475US3DIV	New Application					
			APPLICANT						
LIST OF	REFE	RENCES CITED BY APPLICANT	Kousaku MATSUNO, et al.						
			FILING DATE	GROUP					
			Herewith						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)									
MIC	AAA	T. Ohmi et al.: Native oxide growth and organic impurity removal on Si surface with ozone injected ultrapure water, J. Electrochem. Soc., 140(3), 804-810, 1993							
NIK	AAB	Werner Kern. Handbook of Semiconductor Cleaning Technology, 1993, Noyes Publications, Page 120.							
	AAC								
	AAD								
	AAE								
	AAF								
	AAG								
	AAH								
	AAI								
,	AAJ	the state of the s							
	AAK								
	AAL	4		-					
	AAM								
	AAN								
	AAO	÷							
	AAP	1							
	AAQ		and the second s						
Examiner		a contract -	Dat	e Considered 31/01/05					
*Examiner: Initial if reference is considered, whether ocnot citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									